New Jersey Semi-Conductor Products, Inc.

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OA1182

Gold Bonded Germanium Diode

FEATURES

Low forward voltage drop—low power consumption
Thirty years of proven reliability—one million hours mean time between failures (MTBF)
Very low noise level
Metallurgically bonded

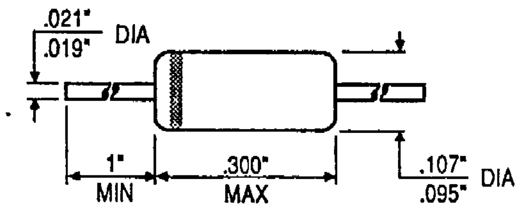
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage	100 Volts
Peak Forward Current	500 mA
Operating Temperature	- 65 °C to 85 °C
Average Power Dissipation	80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	100		V	25 °C
Reverse Current	Ir	60 V		20	µA	25 °C
Forward Voltage	Vf	100 mA		0.85	V	25 °C

MECHANICAL



Quality Semi-Conductors